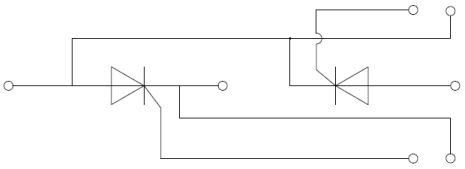
℃		



	℃			
				℃
				℃

FIG 1: Power dissipation vs. on-state current (per thyristor or diode)

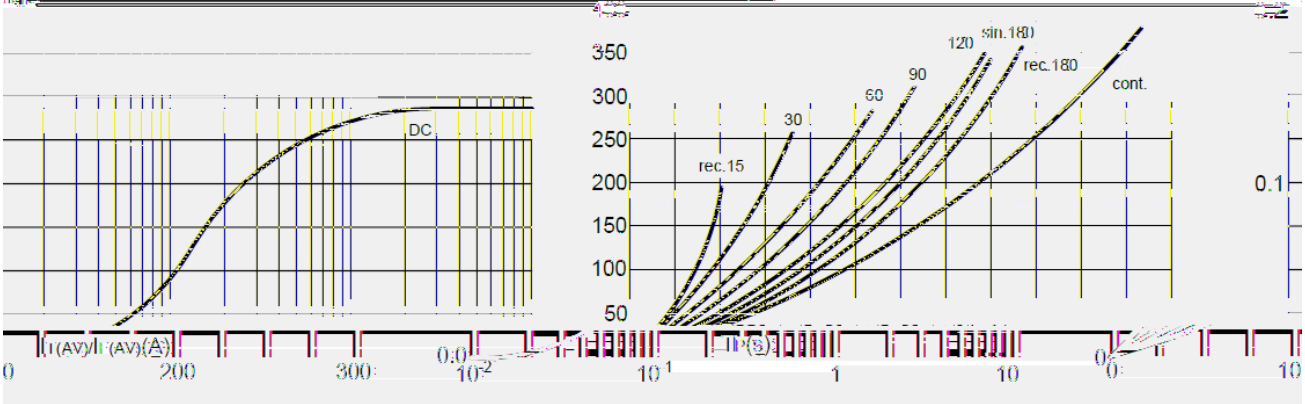


FIG 2: Maximum transient thermal impedance junction to case (per thyristor or diode)

FIG 3: Forward characteristics (per thyristor or diode)

FIG 4: Relative variation of gate trigger current, holding current and latching current versus junction temperature

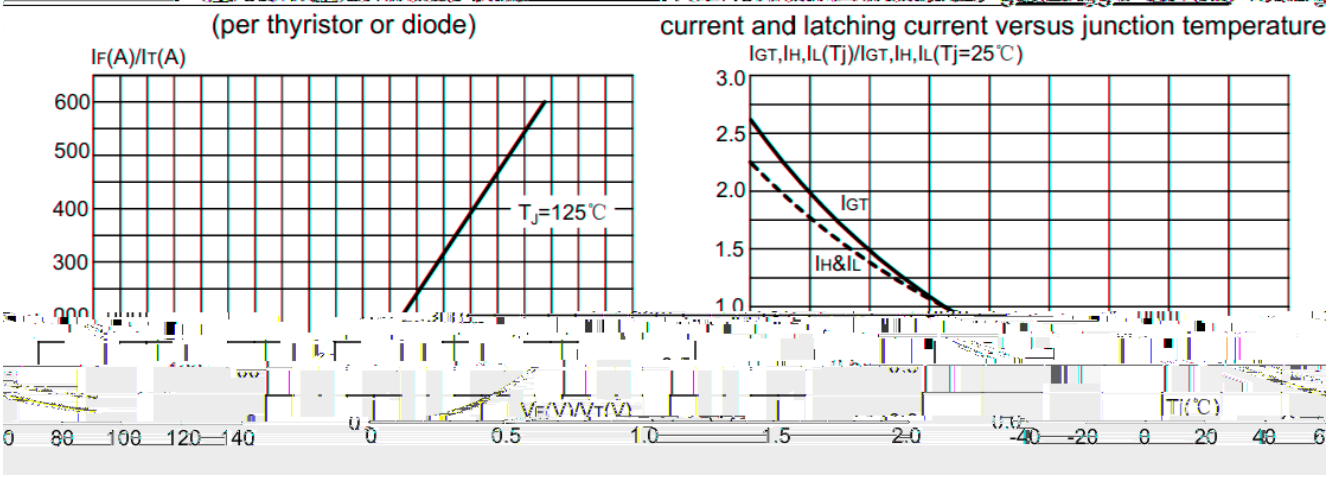


FIG 5 Gate trigger characteristics

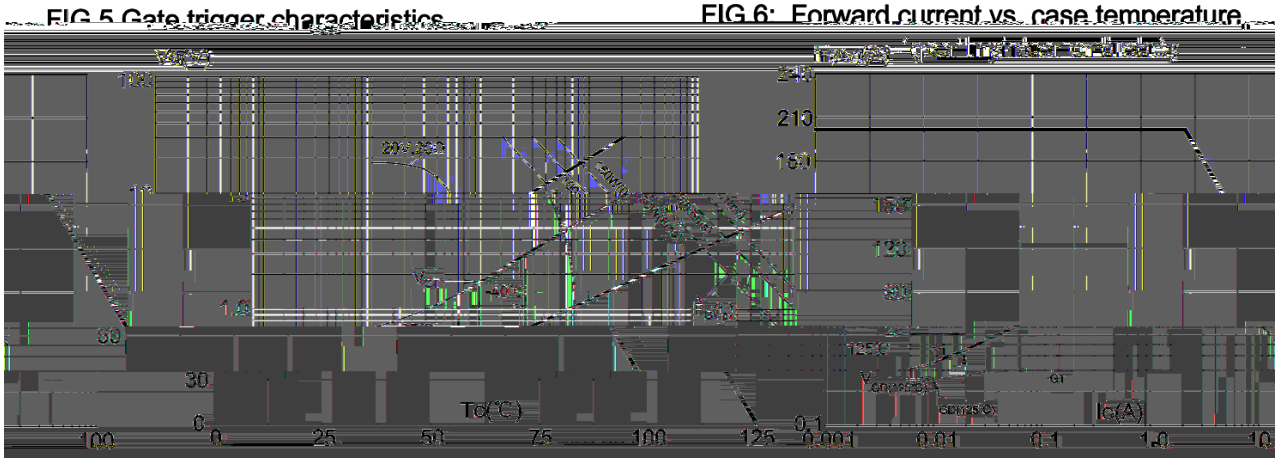
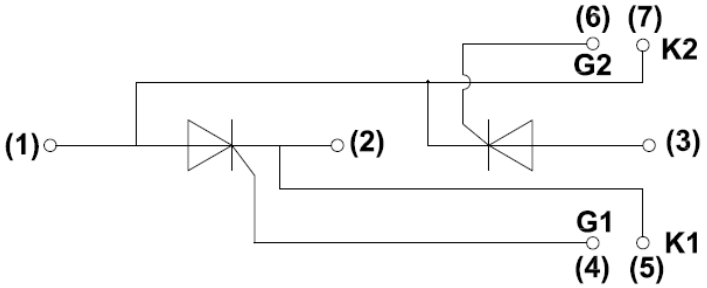
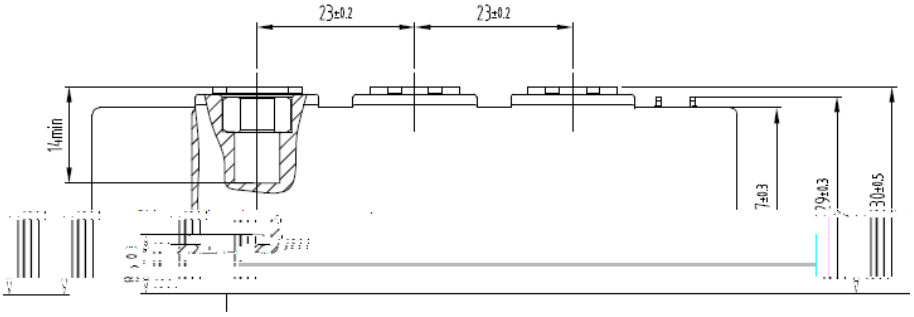
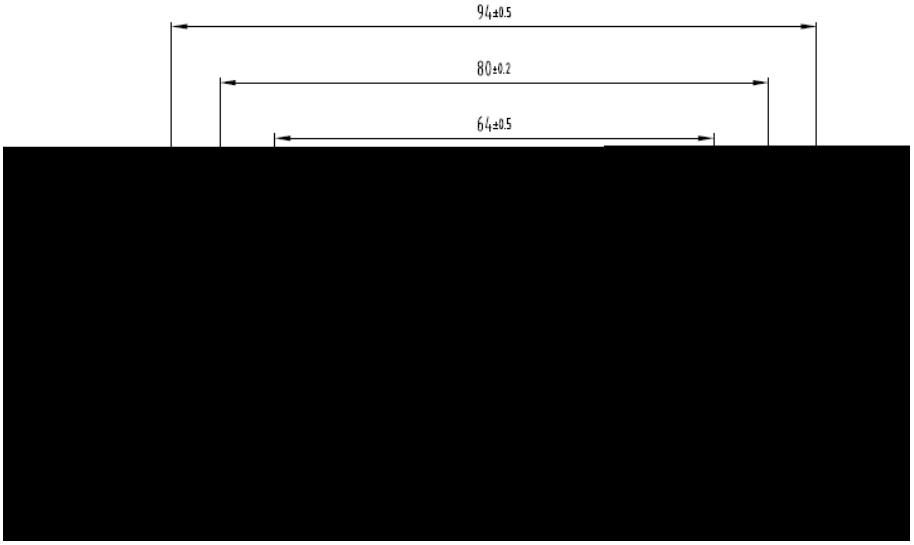


FIG 6: Forward current vs. case temperature (per thyristor or diode)


(6)
(7)
G2
K2
(1)
(2)
(3)
G1
K1
(4)
(5)


23±0.2
23±0.2
14min
7±0.3
29±0.3
30±0.5


94±0.5
80±0.2
64±0.5